

Table of Contents

Introduction	xi
Chapter 1. Active Dopant Profiling in the TEM by Off-Axis Electron Holography	1
David COOPER	
1.1. Introduction	1
1.2. The Basics: from electron waves to phase images	3
1.2.1. Electron holography for the measurement of electromagnetic fields	3
1.2.2. The electron source	6
1.2.3. Forming electron holograms using an electron biprism	6
1.2.4. Care of the electron biprism	10
1.2.5. Recording electron holograms	11
1.2.6. Hologram reconstruction	12
1.2.7. Phase Jumps	15
1.3. Experimental electron holography	16
1.3.1. Fringe contrast, sampling and phase sensitivity	16
1.3.2. Optimizing the beam settings for an electron holography experiment	20
1.3.3. Optimizing the field of view using free lens control	21
1.3.4. Energy filtering for electron holography	24
1.3.5. Minimizing diffraction contrast	25
1.3.6. Measurement of the specimen thickness	26
1.3.7. Specimen preparation	28
1.3.8. The electrically inactive thickness	30
1.4. Conclusion	33
1.5. Bibliography	33

Chapter 2. Dopant Distribution Quantitative Analysis Using STEM-EELS/EDX Spectroscopy Techniques	37
Roland PANTEL and Germain SERVANTON	
2.1. Introduction.	37
2.1.1. Dopant analysis challenges in the silicon industry	37
2.1.2. The different dopant quantification and imaging methods.	38
2.2. STEM-EELS-EDX experimental challenges for quantitative dopant distribution analysis	41
2.2.1. Instrumentation present state-of-the-art and future challenges	41
2.3. Experimental conditions for STEM spectroscopy impurity detection.	43
2.3.1. Radiation damages	43
2.3.2. Particularities of EELS and EDX spectroscopy techniques	44
2.3.3. Equipments used for the STEM-EELS-EDX analyses presented in this chapter.	49
2.4. STEM EELS-EDX quantification of dopant distribution application examples	49
2.4.1. EELS application analysis examples	49
2.4.2. EDX application analysis examples	54
2.5. Discussion on the characteristics of STEM-EELS/EDX and data processing	59
2.6. Bibliography	59
 Chapter 3. Quantitative Strain Measurement in Advanced Devices: A Comparison Between Convergent Beam Electron Diffraction and Nanobeam Diffraction	 65
Laurent CLÉMENT and Dominique DELILLE	
3.1. Introduction.	65
3.2. Electron diffraction technique in TEM (CBED and NBD)	66
3.2.1. CBED patterns acquisition and analysis	66
3.2.2. NBD patterns acquisition and analysis	70
3.3. Experimental details.	71
3.3.1. Instrumentation and setup.	71
3.3.2. Samples description	72
3.4. Results and discussion	72
3.4.1. Strain evaluation in a pMOS transistor integrating eSiGe source and drain – a comparison of CBED and NBD techniques	72
3.4.2. Quantitative strain measurement in advanced devices by NBD	75
3.5. Conclusion	78
3.6. Bibliography	78

Chapter 4. Dark-Field Electron Holography for Strain Mapping	81
Martin HÛTCH, Florent HOUELIER, Nikolay CHERKASHIN, Shay REBOH, Elsa JAVON, Patrick BENZO, Christophe GATEL, Etienne SNOECK and Alain CLAVERIE	
4.1. Introduction.	81
4.2. Setup for dark-field electron holography	83
4.3. Experimental requirements.	85
4.4. Strained silicon transistors with recessed sources and drains stressors	87
4.4.1. Strained silicon p-MOSFET	87
4.5. Thin film effect	92
4.6. Silicon implanted with hydrogen	93
4.7. Strained silicon n-MOSFET	94
4.8. Understanding strain engineering.	96
4.9. Strained silicon devices relying on stressor layers	97
4.10. 28-nm technology node MOSFETs	99
4.11. FinFET device	101
4.12. Conclusions	103
4.13. Bibliography	103
 Chapter 5. Magnetic Mapping Using Electron Holography	 107
Etienne SNOECK and Christophe GATEL	
5.1. Introduction.	107
5.2. Experimental	108
5.2.1. The Lorentz mode	110
5.2.2 The “ ϕ^{E_s} ” problem.	111
5.3. Hologram analysis: from the phase images to the magnetic properties	118
5.3.1. The simplest case: homogeneous specimen of constant thickness	119
5.3.2. The general case	122
5.4. Resolutions	124
5.4.1. Magnetic measurements accuracy	124
5.4.2. Spatial resolution	126
5.5. One example: FePd (L10) epitaxial thin film exhibiting a perpendicular magnetic anisotropy (PMA)	126
5.6. Prospective and new developments.	130
5.6.1. Enhanced signal and resolution.	130
5.6.2. In-situ switching	131
5.7. Conclusions.	132
5.8. Bibliography	133

Chapter 6. Interdiffusion and Chemical Reaction at Interfaces by TEM/EELS	135
Sylvie SCHAMM-CHARDON	
6.1. Introduction.	135
6.2. Importance of interfaces in MOSFETs.	135
6.3. TEM and EELS	137
6.4. TEM/EELS and study of interdiffusion/chemical reaction at interfaces in microelectronics	137
6.4.1. Thickness measurement	138
6.4.2. Atomic structure analysis	139
6.4.3. EELS analysis	141
6.4.4. Sample preparation	143
6.5. HRTEM/EELS as a support to developments of RE- and TM-based HK thin films on Si and Ge	144
6.5.1. Introduction	144
6.5.2. HRTEM/EELS methodology	145
6.5.3. Illustrations	154
6.6. Conclusion	158
6.7. Bibliography	158
Chapter 7. Characterization of Process-Induced Defects.	165
Nikolay CHERKASHIN and Alain CLAVERIE.	
7.1. Interfacial dislocations	166
7.1.1. Si(100)/Si(100) direct wafer bonding (DWB)	167
7.1.2. SiGe heterostructures	170
7.2. Ion implantation induced defects	172
7.2.1. Defects of interstitial type	173
7.2.2. Defects of vacancy type	187
7.3. Conclusions.	193
7.4. Bibliography	193
Chapter 8. <i>In Situ</i> Characterization Methods in Transmission Electron Microscopy	199
Aurélien MASSEBOEUF	
8.1. Introduction.	199
8.2. <i>In situ</i> in a TEM	200
8.2.1. Temperature control and irradiation	201
8.2.2. Electromagnetic field	201
8.2.3. Mechanical.	202
8.2.4. Chemistry	202
8.2.5. Light	203
8.2.6. Multiple and movable currents	203

8.3. Biasing in a conventional TEM	204
8.3.1. Multiple contacts	204
8.3.2. Movable contacts	206
8.3.3. Comparison	206
8.4. Sample design	208
8.4.1. Focused ion beam.	208
8.4.2. TEM windows.	209
8.5. Conclusions.	211
8.6. Bibliography	211
Chapter 9. Specimen Preparation for Semiconductor Analysis.	219
David COOPER and Gérard BEN ASSAYAG	
9.1. The focused ion beam tool	220
9.2. Ion-sample interaction	221
9.3. Beam currents and energies for specimen preparation.	225
9.4. Practical specimen preparation	228
9.5. In situ lift-out.	228
9.6. H-bar technique	232
9.7. Broad beam ion milling.	233
9.8. Mechanical wedge polishing.	235
9.9. Conclusion	235
9.10 Bibliography.	236
List of Authors	237
Index	241